



Low Power, Rail-to-Rail Output Precision JFET Amplifier

AD8641

FEATURES

- Low supply current: 250 μ A max
- Very low input bias current: 1 pA max
- Low offset voltage: 750 μ V max
- Single-supply operation: 5 V to 26 V
- Dual-supply operation: \pm 2.5 V to \pm 13 V
- Rail-to-rail output
- Unity gain stable
- No phase reversal
- SC70 package

APPLICATIONS

- Line-/battery-powered instruments
- Photodiode amplifiers
- Precision current sensing
- Medical instrumentation
- Industrial controls
- Precision filters
- Portable audio
- ATE

GENERAL DESCRIPTION

The AD8641 is a low power, precision JFET input amplifier featuring extremely low input bias current and rail-to-rail output. The ability to swing nearly rail-to-rail at the input and rail-to-rail at the output enables designers to buffer CMOS DACs, ASICs, and other wide output swing devices in single-supply systems. The outputs remain stable with capacitive loads of more than 500 pF.

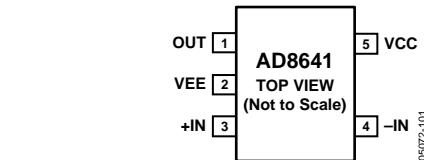


Figure 1. 5-Lead SC70 (KS-5)

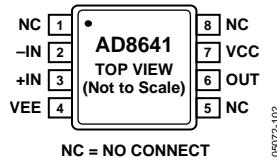


Figure 2. 8-Lead SOIC (R-8)

The AD8641 is suitable for applications utilizing multichannel boards that require low power to manage heat. Other applications include photodiodes, ATE reference level drivers, battery management, and industrial controls.

The AD8641 is fully specified over the extended industrial temperature range of -40° to $+125^{\circ}$ C. The AD8641 is available in 5-lead SC70 and 8-lead SOIC lead-free packages.

Rev. 0

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REVISION HISTORY

10/04—Initial Version: Revision 0

SPECIFICATIONS

ELECTRICAL CHARACTERISTICS

@ $V_S = 5.0$ V, $V_{CM} = 2.5$ V, $T_A = 25^\circ\text{C}$, unless otherwise noted.

Table 1.

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
INPUT CHARACTERISTICS						
Offset Voltage	V_{OS}	$-40^\circ\text{C} < T_A < +85^\circ\text{C}$ $+85^\circ\text{C} < T_A < +125^\circ\text{C}, V_{CM} = 1.5$ V	50	750	1.5	μV
Input Bias Current	I_B	$-40^\circ\text{C} < T_A < +125^\circ\text{C}$	0.25	1	1.6	mA
Input Offset Current	I_{OS}	$-40^\circ\text{C} < T_A < +125^\circ\text{C}$	180	0.5	50	pA
Input Voltage Range			0	3		V
Common-Mode Rejection Ratio	CMRR	$V_{CM} = 0$ V to 2.5 V	74	93		dB
Large Signal Voltage Gain	A_V	$R_L = 10 \text{ k}\Omega, V_O = 0.5$ to 4.5 V	80	140		V/mV
Offset Voltage Drift	$\Delta V_{OS}/\Delta T$	$-40^\circ\text{C} < T_A < +125^\circ\text{C}$	2.5			$\mu\text{V}/^\circ\text{C}$
OUTPUT CHARACTERISTICS						
Output Voltage High	V_{OH}	$I_L = 2 \text{ mA}, -40^\circ\text{C} \text{ to } +125^\circ\text{C}$	4.94			V
Output Voltage Low	V_{OL}	$I_L = 2 \text{ mA}, -40^\circ\text{C} \text{ to } +125^\circ\text{C}$	4.93	0.05	0.01	V
Output Current	I_{OUT}			±6	0.05	mA
POWER SUPPLY						
Power Supply Rejection Ratio	PSRR	$V_S = 5$ V to 26 V	90	107		dB
Supply Current/Amplifier	I_{SY}	$-40^\circ\text{C} < T_A < +125^\circ\text{C}$	195	250	270	μA
DYNAMIC PERFORMANCE						
Slew Rate	SR		2			$\text{V}/\mu\text{s}$
Gain Bandwidth Product	GBP		3			MHz
Phase Margin	\emptyset_o		50			Degrees
NOISE PERFORMANCE						
Voltage Noise	e_N p-p	$f = 0.1$ Hz to 10 Hz	4.0			μV p-p
Voltage Noise Density	e_N	$f = 1$ kHz	28.5			$\text{nV}/\sqrt{\text{Hz}}$
Current Noise Density	i_N	$f = 1$ kHz	0.5			$\text{fA}/\sqrt{\text{Hz}}$

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@ $V_S = \pm 13$ V, $V_{CM} = 0$ V, $T_A = 25^\circ\text{C}$, unless otherwise noted.

Table 2.

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
INPUT CHARACTERISTICS						
Offset Voltage	V_{OS}	$-40^\circ < T_A < +125^\circ\text{C}$	70	750		μV
					1.5	mV
Input Bias Current	I_B	$-40^\circ\text{C} < T_A < +125^\circ\text{C}$		0.25	1	pA
					260	pA
Input Offset Current	I_{OS}	$-40^\circ\text{C} < T_A < +125^\circ\text{C}$			0.5	pA
					35	pA
Input Voltage Range			-13		+10	V
Common-Mode Rejection Ratio	CMRR	$V_{CM} = -13$ V to +10 V	90	107		dB
Large Signal Voltage Gain	A_{VO}	$R_L = 10 \text{ k}\Omega$, $V_O = -11$ V to +11 V	215	290		V/mV
Offset Voltage Drift	$\Delta V_{OS}/\Delta T$	$-40^\circ\text{C} < T_A < +125^\circ\text{C}$			2.5	$\mu\text{V}/^\circ\text{C}$
OUTPUT CHARACTERISTICS						
Output Voltage High	V_{OH}		+12.94			V
		$I_L = 2 \text{ mA}$, -40°C to +125°C	+12.93			V
Output Voltage Low	V_{OL}			+12.94		V
		$I_L = 2 \text{ mA}$, -40°C to +125°C		-12.93		V
Output Current	I_{OUT}			± 12		mA
POWER SUPPLY						
Power Supply Rejection Ratio	PSRR	$V_S = \pm 2.5$ V to ± 13 V	90	107		dB
Supply Current/Amplifier	I_{SY}	$-40^\circ\text{C} < T_A < +125^\circ\text{C}$		200	290	μA
					330	μA
DYNAMIC PERFORMANCE						
Slew Rate	SR			3		$\text{V}/\mu\text{s}$
Gain Bandwidth Product	GBP			3.5		MHz
Phase Margin	\emptyset_o			60		Degrees
NOISE PERFORMANCE						
Voltage Noise	$e_N \text{ p-p}$	$f = 0.1 \text{ Hz}$ to 10 Hz		4.2		$\mu\text{V p-p}$
Voltage Noise Density	e_N	$f = 1 \text{ kHz}$		27.5		$\text{nV}/\sqrt{\text{Hz}}$
Current Noise Density	i_N	$f = 1 \text{ kHz}$		0.5		$\text{fA}/\sqrt{\text{Hz}}$

ABSOLUTE MAXIMUM RATINGS

Table 3. Absolute Maximum Ratings¹

Parameter	Rating
Supply Voltage	27.3 V
Input Voltage	VS– to VS+
Differential Input Voltage	±Supply Voltage
Output Short-Circuit Duration	Indefinite
Storage Temperature Range KS-5, R-8 Packages	–65°C to +150°C
Operating Temperature Range	–40°C to +125°C
Junction Temperature Range KS-5, R-8 Packages	–65°C to +150°C
Lead Temperature Range (Soldering, 60 Sec)	300°C

Table 4.

Package Type	θ_{JA} ²	θ_{JC}	Units
5-Lead SC70 (KS-5)	331.4	223.9	°C/W
8-Lead SOIC (R-8)	157	56	°C/W

Stresses above those listed under Absolute Maximum Ratings may cause permanent damage to the device. This is a stress rating only; functional operation of the device at these or any other conditions above those listed in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

¹ Absolute maximum ratings apply at 25°C, unless otherwise noted.

² θ_{JA} is specified for the worst-case conditions, i.e., θ_{JA} is specified for devices soldered on circuit boards for surface-mounted packages.

ESD CAUTION

ESD (electrostatic discharge) sensitive device. Electrostatic charges as high as 4000 V readily accumulate on the human body and test equipment and can discharge without detection. Although this product features proprietary ESD protection circuitry, permanent damage may occur on devices subjected to high energy electrostatic discharges. Therefore, proper ESD precautions are recommended to avoid performance degradation or loss of functionality.



TYPICAL PERFORMANCE CHARACTERISTICS

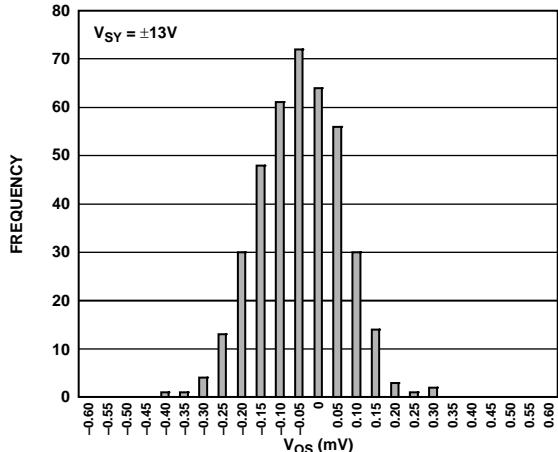


Figure 3. Input Offset Voltage

05072-002

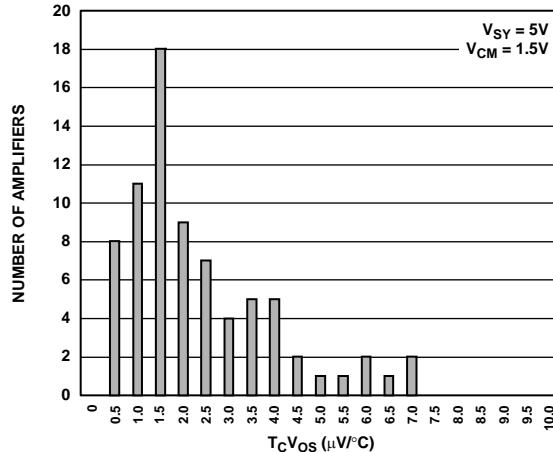


Figure 6. Offset Voltage Drift

05072-005

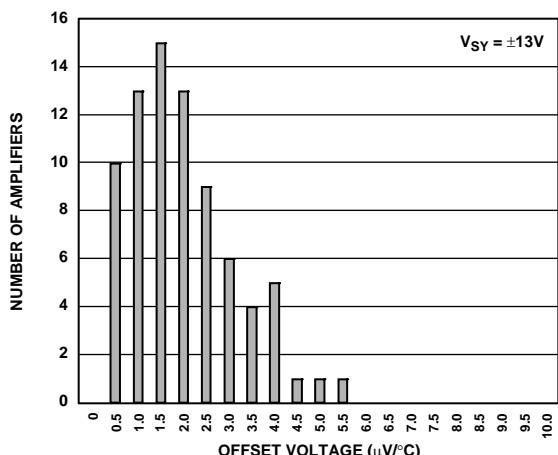
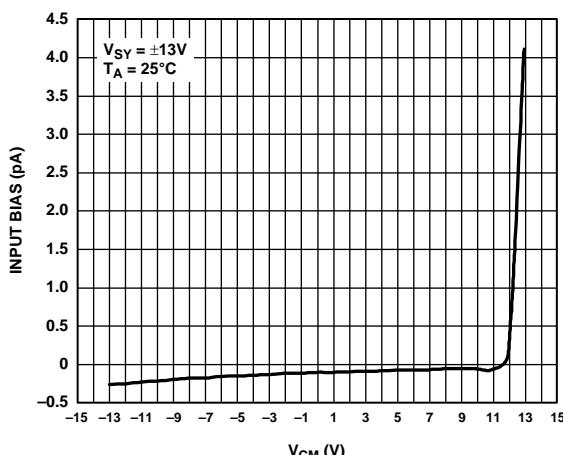


Figure 4. Offset Voltage Drift

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Figure 7. Input Bias Current vs. V_{CM}

05072-006

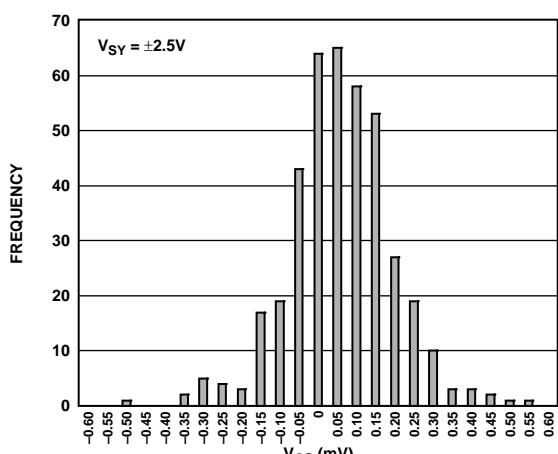
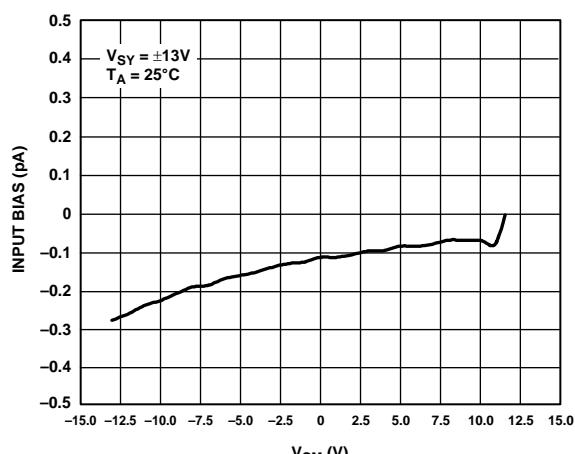
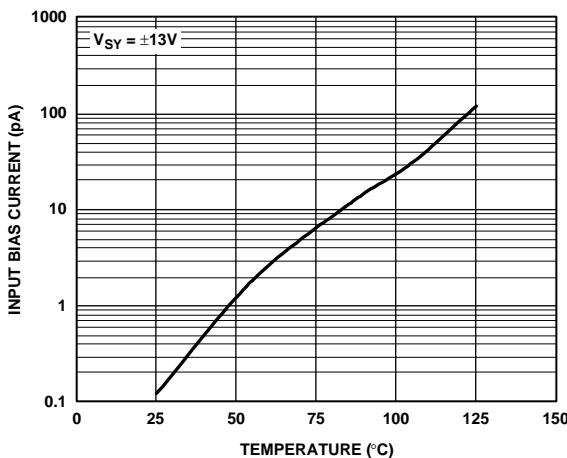


Figure 5. Input Offset Voltage

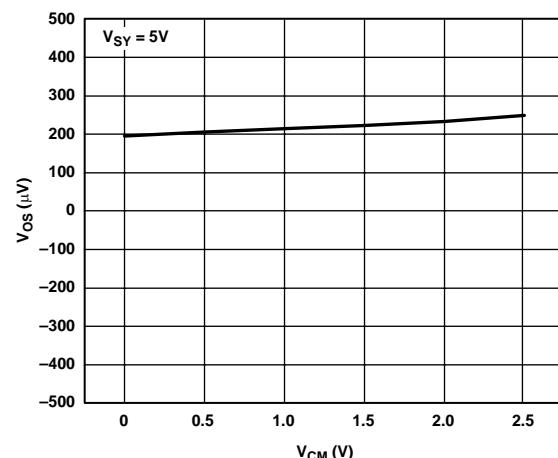
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Figure 8. Input Bias Current vs. V_{CM}

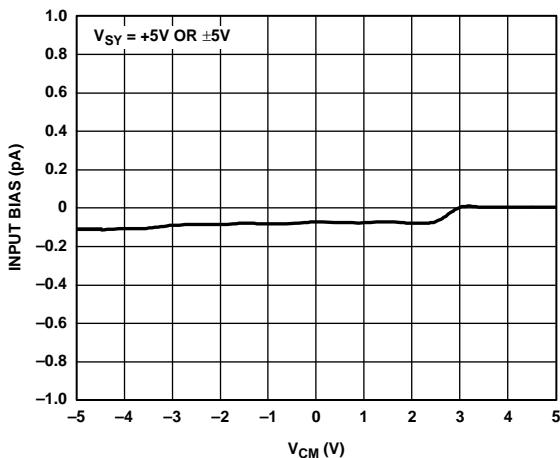
05072-007



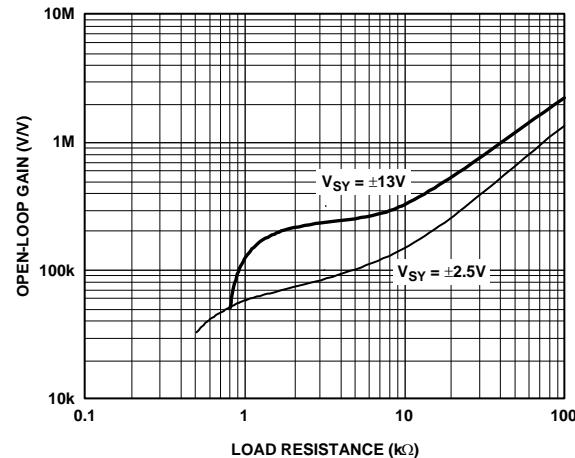
05072-008



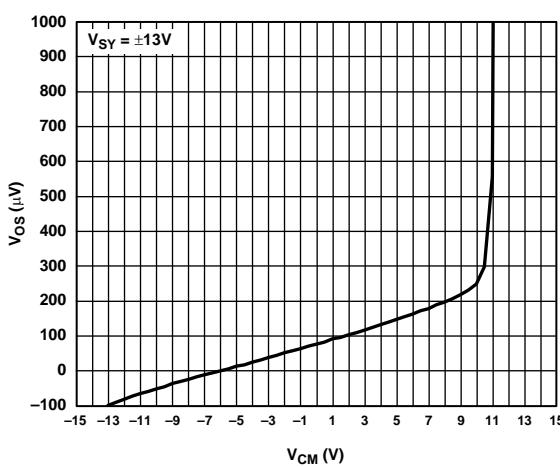
05072-011



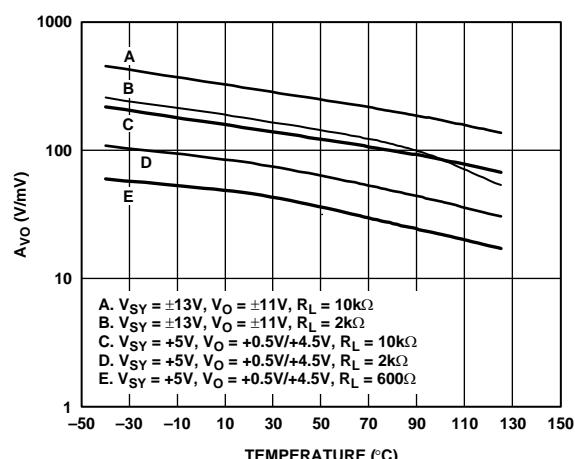
05072-009



05072-012



05072-010



05072-013

Figure 14. Open-Loop Gain vs. Temperature

AD8641

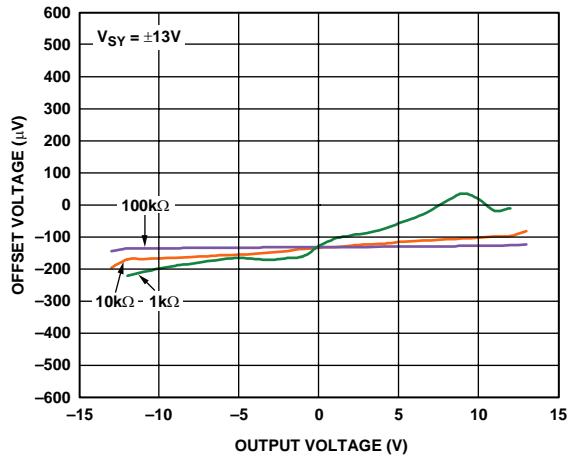


Figure 15. Input Error Voltage vs. Output Voltage for Resistive Loads

05072-014

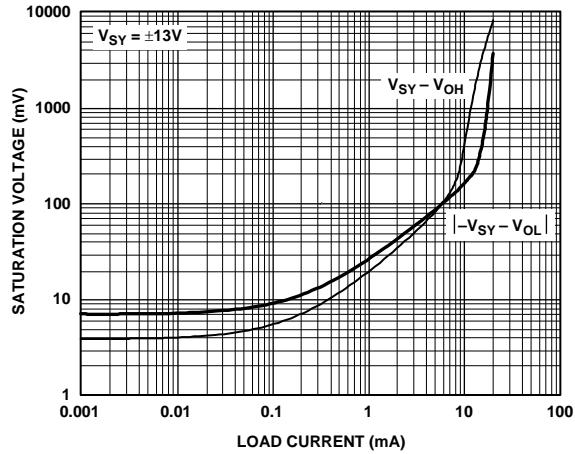


Figure 18. Output Saturation Voltage vs. Load Current

05072-017

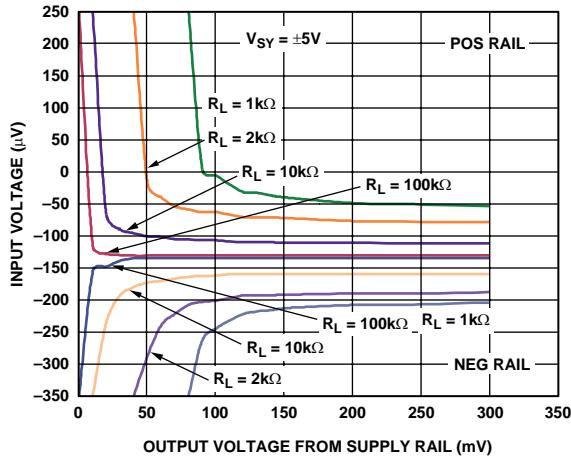


Figure 16. Input Error Voltage vs. Output Voltage Within 300 mV of Supply Rails

05072-015

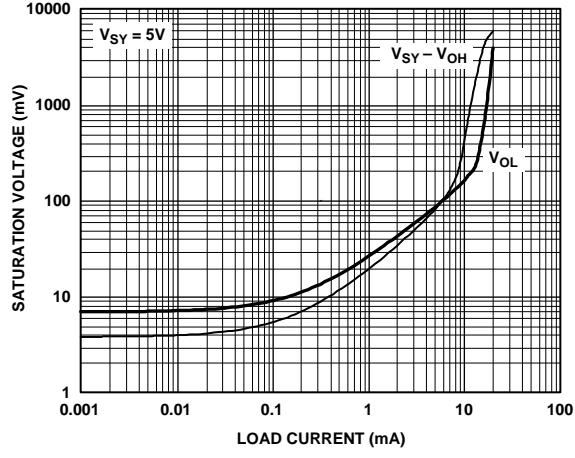


Figure 19. Output Saturation Voltage vs. Load Current

05072-018

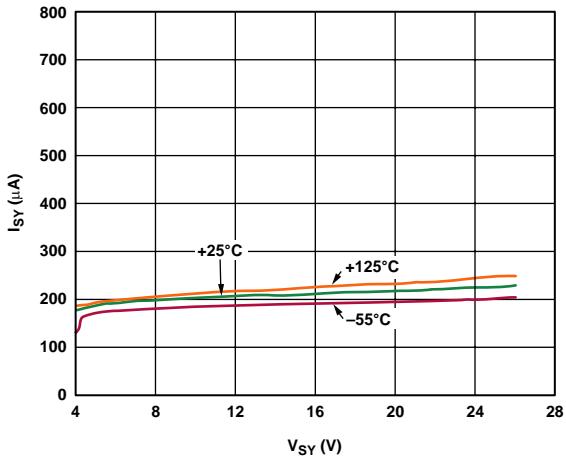


Figure 17. Quiescent Current vs. Supply Voltage at Different Temperatures

05072-016

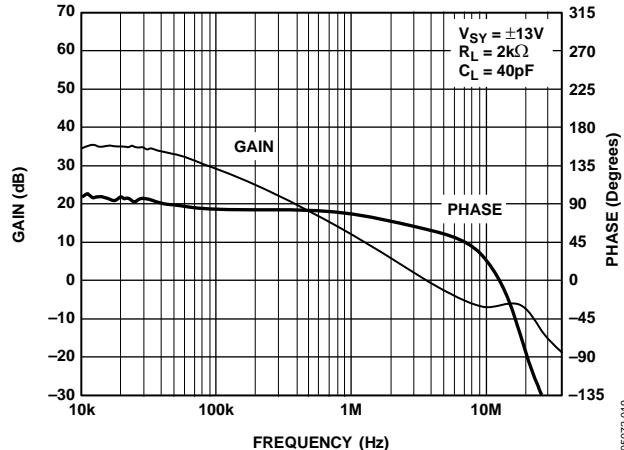
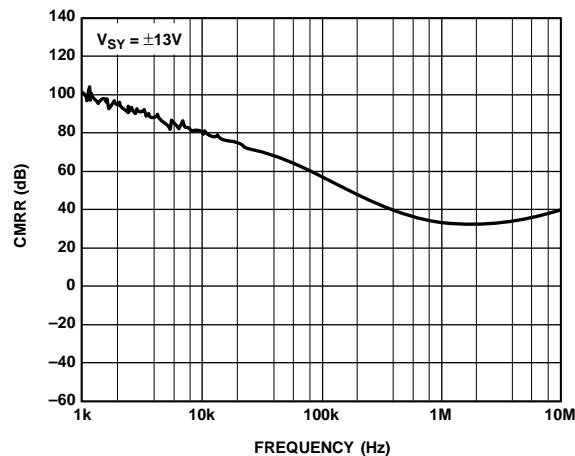
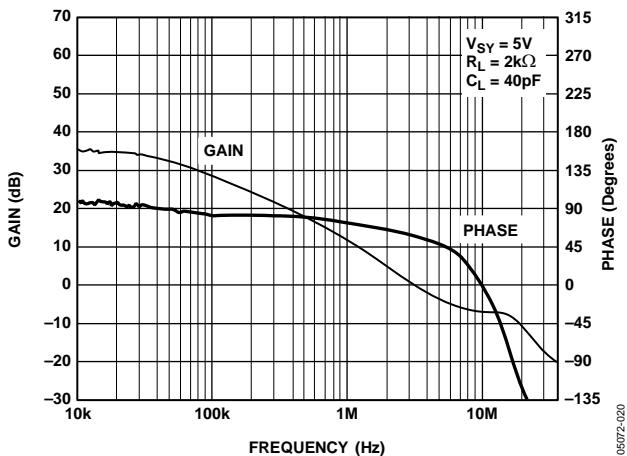
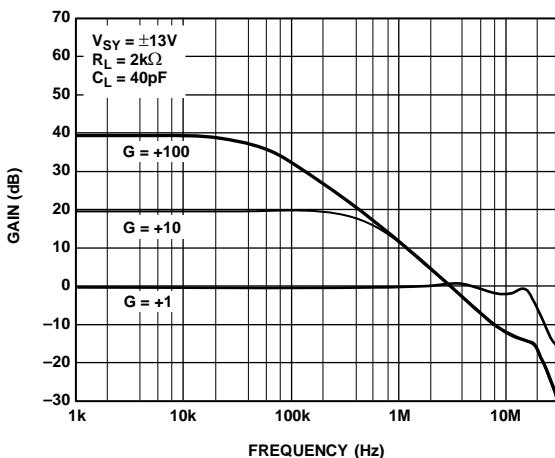


Figure 20. Open-Loop Gain and Phase Margin vs. Frequency

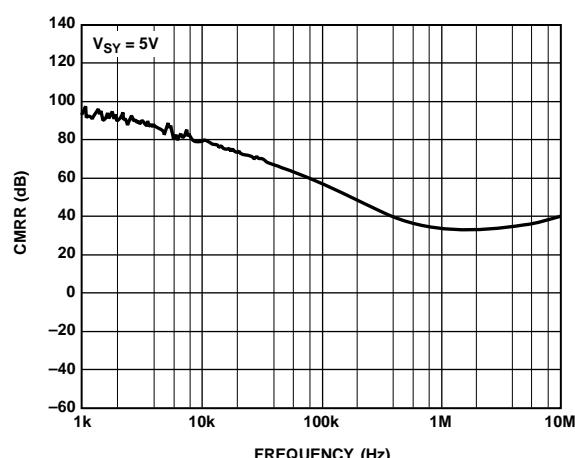
05072-019



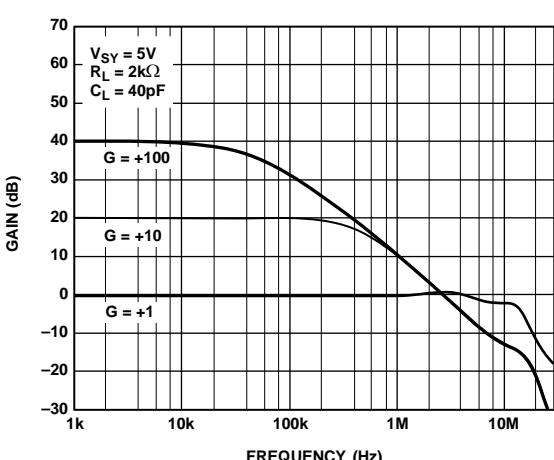
05072-021



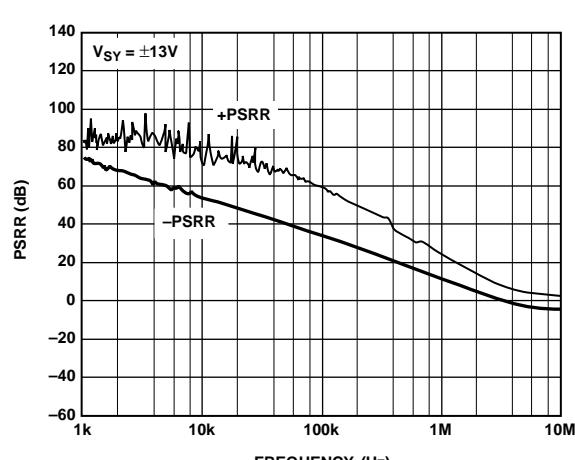
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05072-022



05072-025

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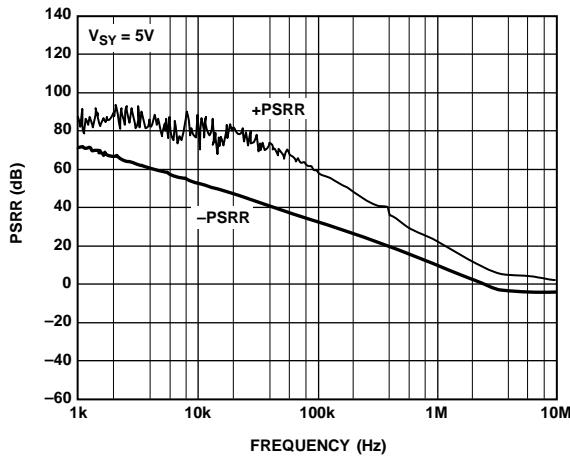


Figure 27. PSRR vs. Frequency

05072-026

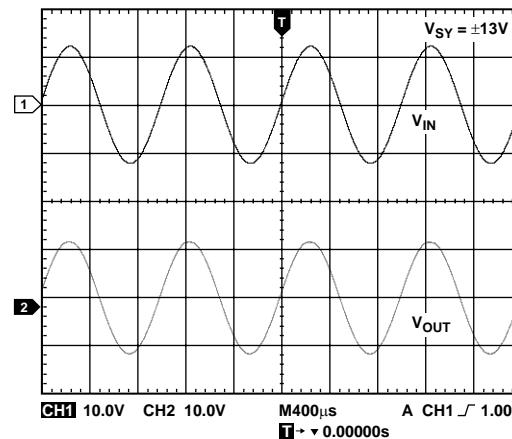


Figure 30. No Phase Reversal

05072-029

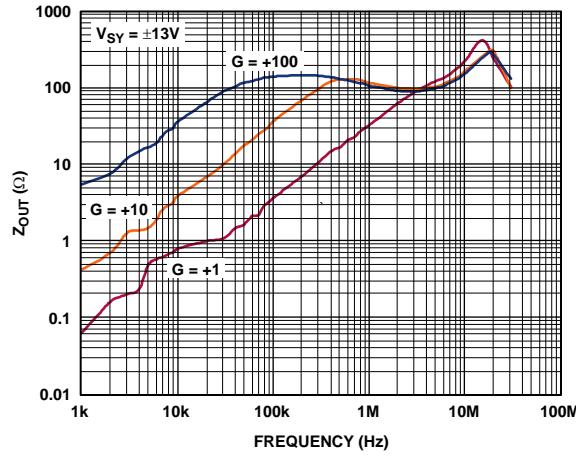


Figure 28. Output Impedance vs. Frequency

05072-027

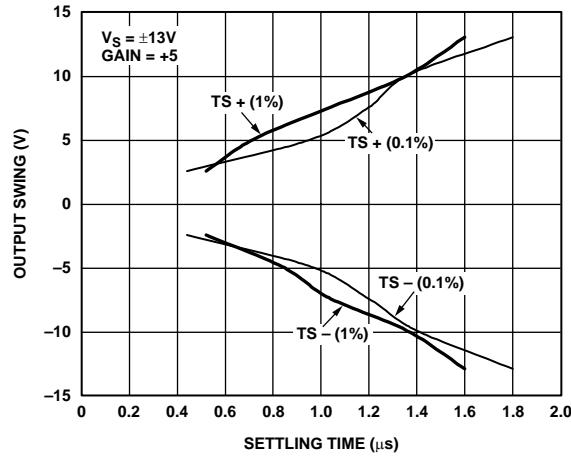


Figure 31. Output Swing and Error vs. Settling Time

05072-030

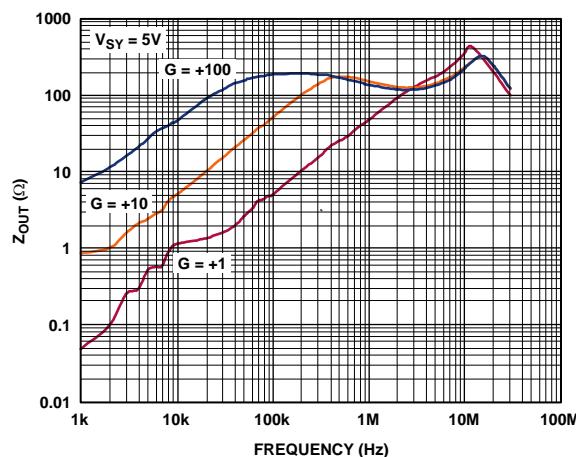


Figure 29. Output Impedance vs. Frequency

05072-028

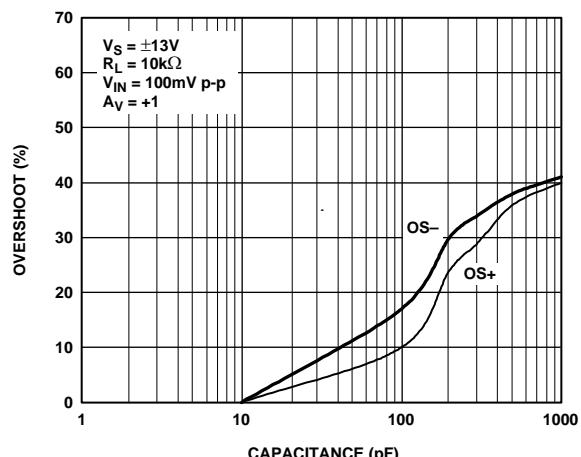
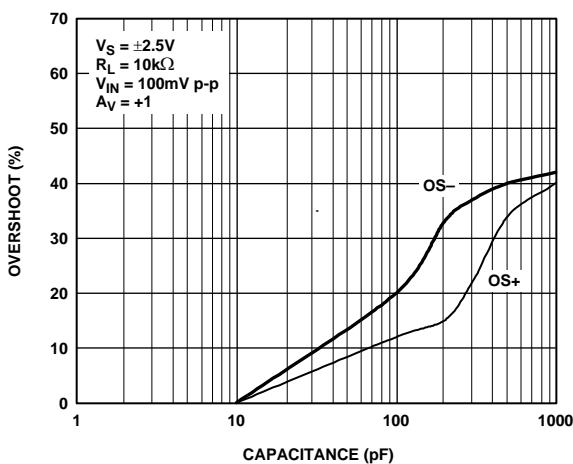
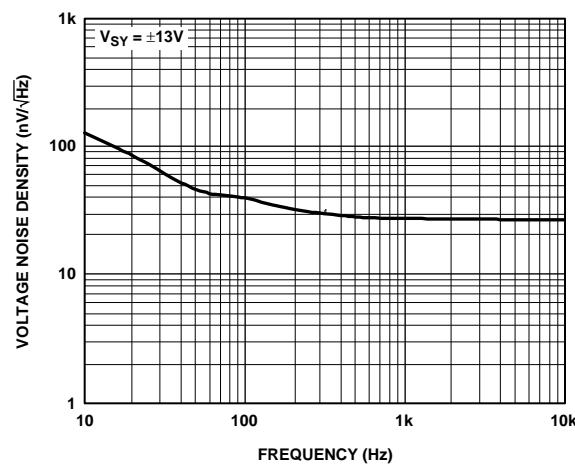


Figure 32. Small Signal Overshoot vs. Load Capacitance

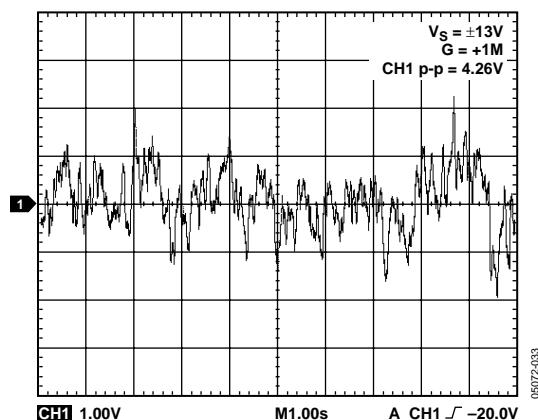
05072-031



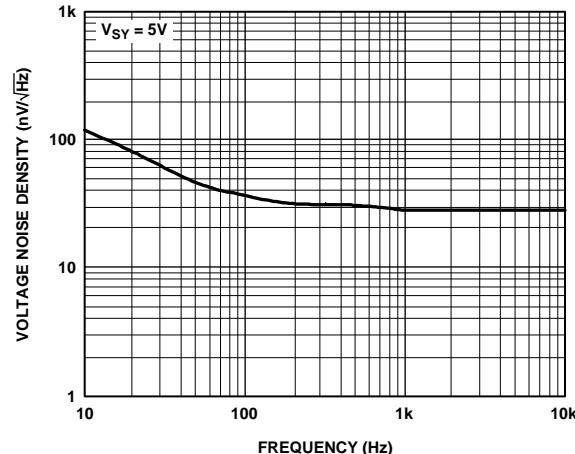
05072-032



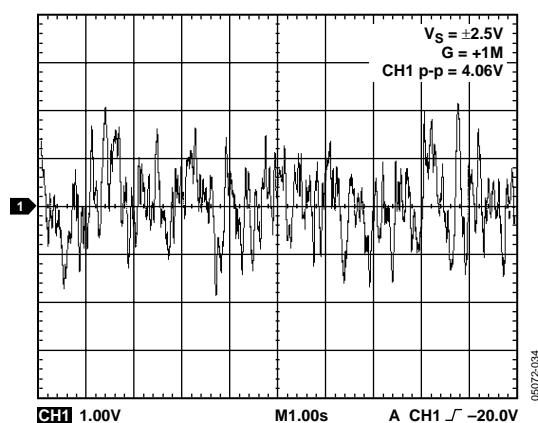
05072-035



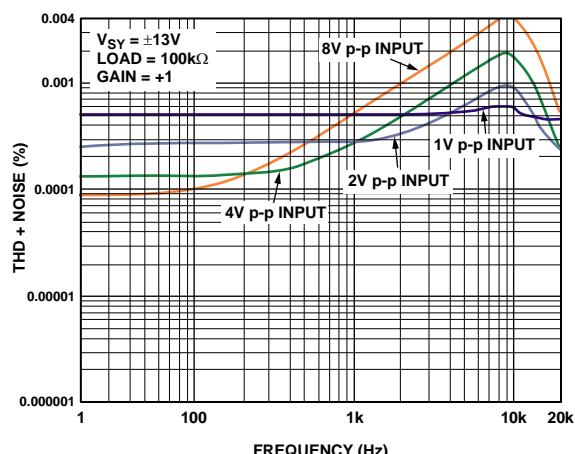
05072-033



05072-036



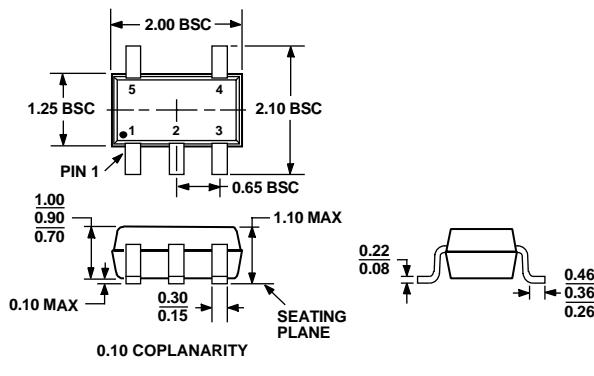
05072-034



05072-037

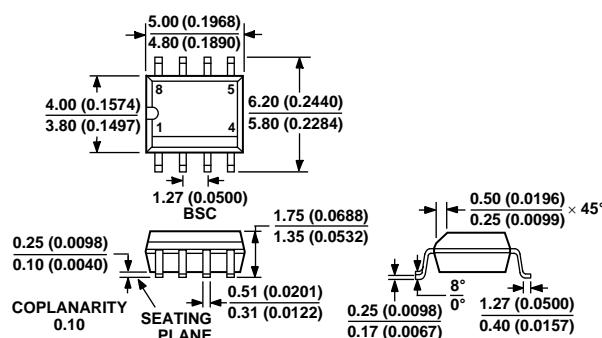
*Figure 33. Small Signal Overshoot vs. Load Capacitance**Figure 36. Voltage Noise Density*

OUTLINE DIMENSIONS



COMPLIANT TO JEDEC STANDARDS MO-203AA

Figure 39. 5-Lead Thin Shrink Small Outline Transistor Package [SC70]
(KS-5)
Dimensions shown in millimeters



COMPLIANT TO JEDEC STANDARDS MS-012AA
CONTROLLING DIMENSIONS ARE IN MILLIMETERS; INCH DIMENSIONS
(IN PARENTHESES) ARE ROUNDED-OFF MILLIMETER EQUIVALENTS FOR
REFERENCE ONLY AND ARE NOT APPROPRIATE FOR USE IN DESIGN

Figure 40. 8-Lead Standard Small Outline Package [SOIC]
(R-8)
Dimensions shown in millimeters

ORDERING GUIDE

Model	Temperature Range	Package Description	Package Option	Branding
AD8641AKSZ-R2 ¹	-40°C to +125°C	5-Lead SC70	KS-5	A07
AD8641AKSZ-Reel7 ¹	-40°C to +125°C	5-Lead SC70	KS-5	A07
AD8641AKSZ-Reel ¹	-40°C to +125°C	5-Lead SC70	KS-5	A07
AD8641ARZ ¹	-40°C to +125°C	8-lead SOIC	R-8	
AD8641ARZ-Reel7 ¹	-40°C to +125°C	8-lead SOIC	R-8	
AD8641ARZ-Reel ¹	-40°C to +125°C	8-lead SOIC	R-8	

¹ Z = Pb-free part.